/ Descriptions

SOT23-6 P MOS

Dual P-Channel MOSFET in a SOT23-6 Plastic Package.

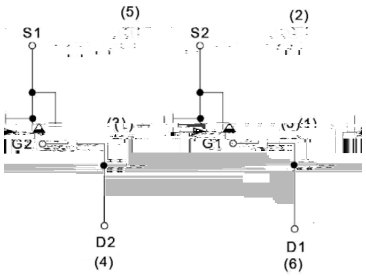
/ Features

Super high dense cell design for low $R_{DS(ON)}$,Rugged and reliable. HF product.

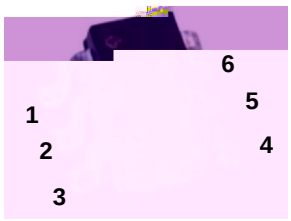
/ Applications

Power Management in Notebook computer, Portable Equipment and Battery powered systems.

/ Equivalent Circuit



/ Pinning



PIN1 G1 PIN 2 S2 PIN 3 G2

PIN 4 D2 PIN 5 S1 PIN 6 D1

/ Marking

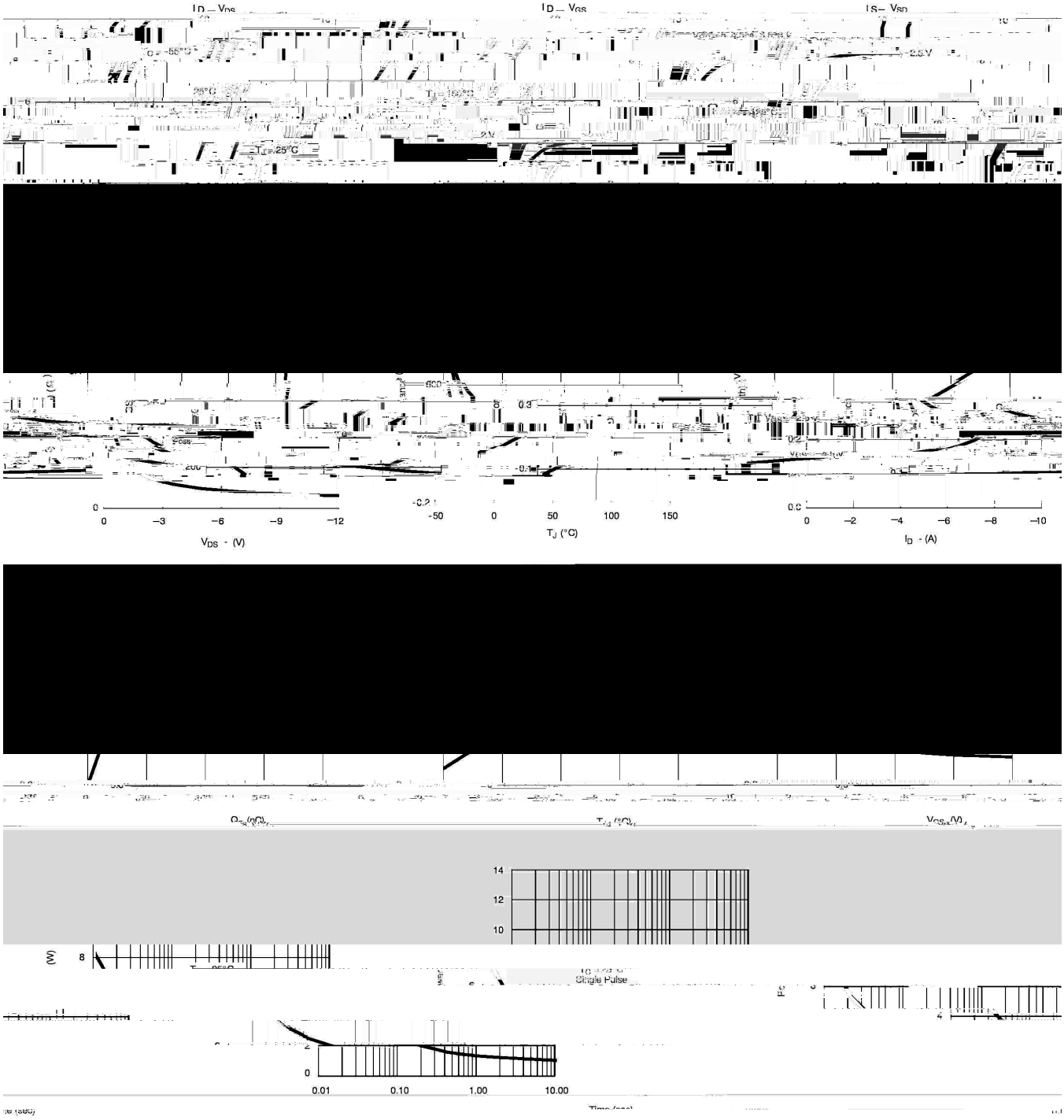
See Marking Instructions

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	-20	V
Gate-Source Voltage	V_{GSS}	±12	V
Continuous Drain Current	I_D *	-3.0	A

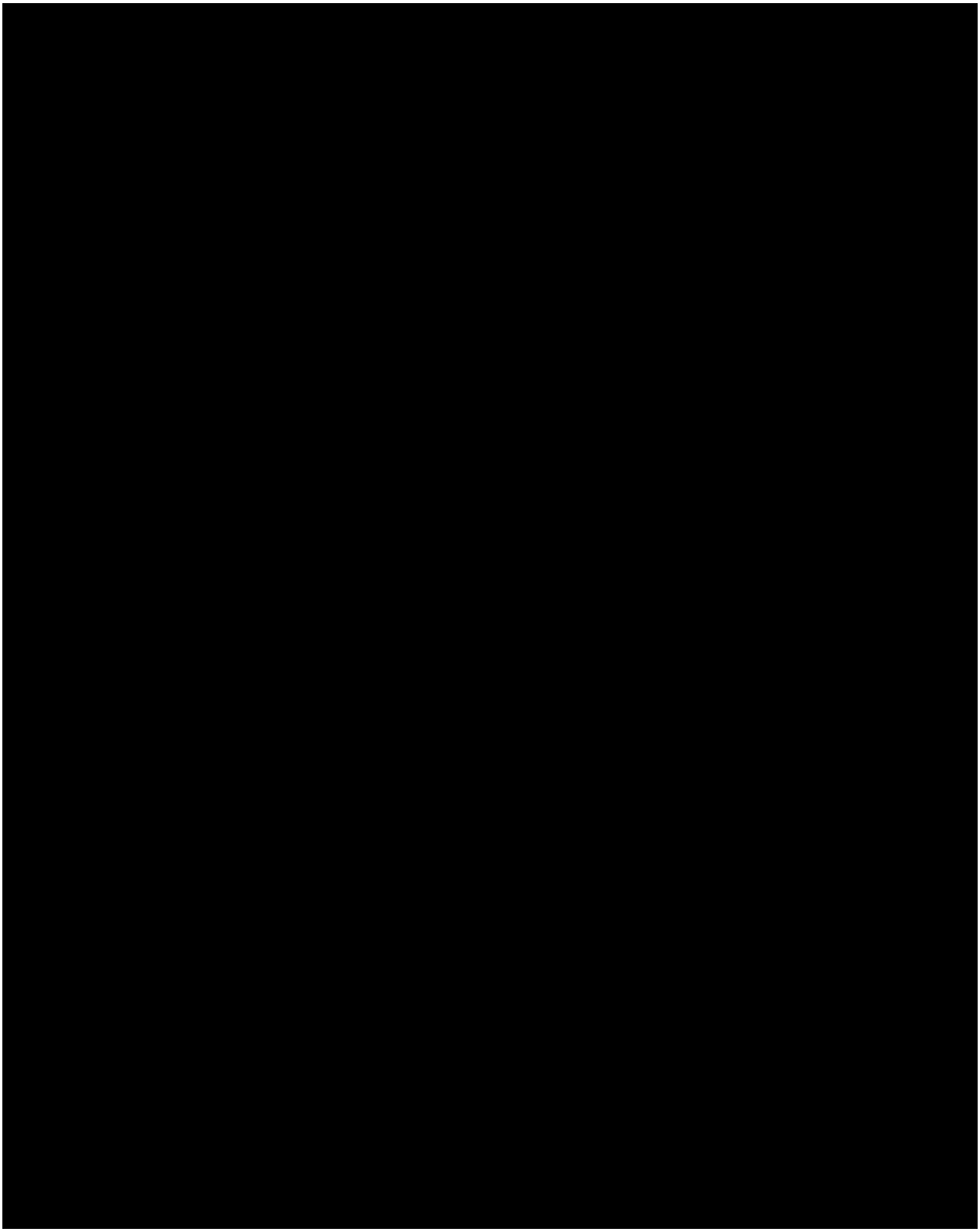
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ

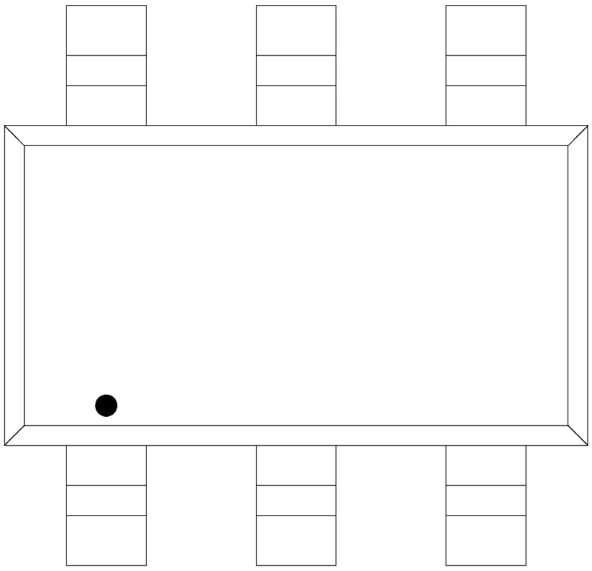
/ Electrical Characteristic Curve



/ Package Dimensions



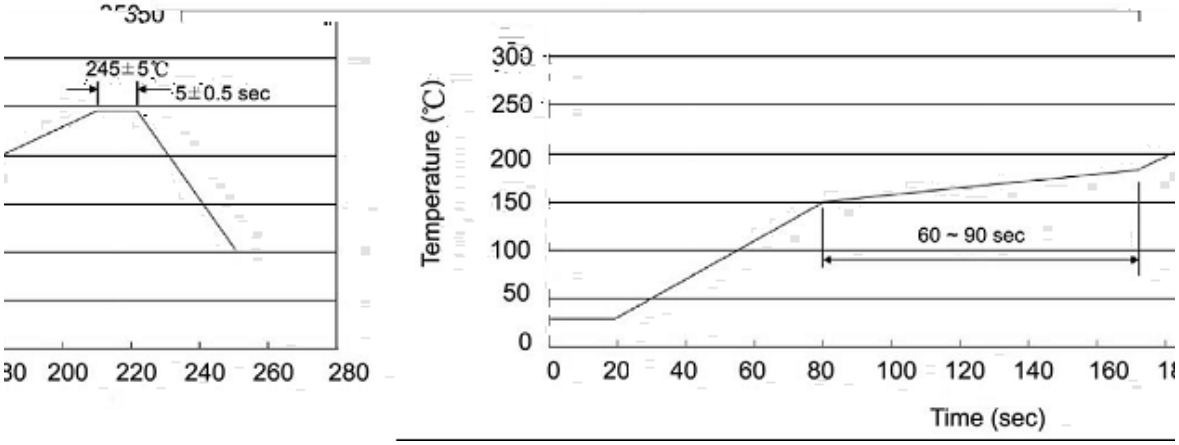
/ Marking Instructions



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( ) / Wh p shrdwxrh Prriioh irr IU Uhiorw Vroghriqj+Pe-Frhh,



Note:

1	150	180	60	90sec;	1.Preheating:150~180 , Time:60~90sec.
2	245±5			5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.
3		2	10	/sec.	3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260±5	10±1 sec.	Temp.:260±5	Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)	
	只 卷盘	卷盘 盒	只 盒	盒 箱	只 箱	盒	箱